

Synthesis and Structure of Alkaline Earth Silicon Nitrides: BaSiN₂, SrSiN₂, and CaSiN₂

Zoltán A. Gál, Phillip M. Mallinson, Heston J. Orchard, and Simon J. Clarke*

Inorganic Chemistry Laboratory, Department of Chemistry, University of Oxford, South Parks Road, Oxford OX1 3QR, U.K.

Received January 26, 2004

The alkaline earth silicon nitrides $AE\text{SiN}_2$ ($AE = \text{Ca}, \text{Sr}, \text{Ba}$) are reported, synthesized as clear, colorless, single crystals from molten sodium at 900–1100 °C or, in the cases of BaSiN₂ and SrSiN₂, as white powders by reacting powdered intermetallics $AE\text{Si}$ with flowing anhydrous ammonia at 550–1000 °C. Structures were determined from single-crystal X-ray diffraction measurements at 150 K: BaSiN₂ crystallizes in space group $Cmca$ (No. 64) with $a = 5.6046(1)$ Å, $b = 11.3605(3)$ Å, $c = 7.5851(2)$ Å, and $Z = 8$. The structure consists of pairs of SiN₄ tetrahedra edge-linked to form bow-tie-shaped Si₂N₆ dimers which share vertexes to form layers and has no analogue in oxide chemistry. SrSiN₂ has a distorted form of this structure (SrSiN₂: space group $P2_1/c$ (No. 14), $a = 5.9750(5)$ Å, $b = 7.2826(7)$ Å, $c = 5.4969(4)$ Å, $\beta = 113.496(4)^\circ$, $Z = 4$). The structure of CaSiN₂ contains only vertex-sharing SiN₄ tetrahedra, linked to form a three-dimensional stuffed-cristobalite type framework isostructural with KGaO₂ (CaSiN₂: space group $Pbca$ (No. 61), $a = 5.1229(3)$ Å, $b = 10.2074(6)$ Å, $c = 14.8233(9)$ Å, $Z = 16$).

Introduction

There is an increasing interest in non-oxide solids, and some nitrides and nitride-containing compounds have important electronic or structural properties complementary to those of oxides. Silicon nitride, Si₃N₄, is an important ceramic material,^{1,2} and there exist also a wide range of ternary nitridosilicates containing a formally anionic SiN_x^{(3x-4)-} framework and electropositive counteranions. Many of these materials have been synthesized in the group of Schnick and co-workers³ by the reaction between alkaline earth metals and/or lanthanides with silicon diimide at elevated temperatures (e.g. >1500 °C) achieved using a radio frequency induction furnace. In general, silicon adopts tetrahedral coordination in nitrides with the only known exceptions of the recently discovered high-pressure phase $c\text{-Si}_3\text{N}_4$,⁴ with the spinel structure and both SiN₄ tetrahedra and SiN₆ octahedra, and the oxide nitride Ce₁₆Si₁₅O₆N₃₂.⁵ However,

there are important differences between nitridosilicates and the familiar oxosilicate analogues. First, while the Si–O frameworks in oxosilicates contain terminal Si–O bonds or Si–O–Si linkages at the common vertexes of two SiO₄ tetrahedra, nitrogen exhibits a greater range of coordinations by silicon in nitridosilicates. Nitrogen is often found to have three Si neighbors (N^[3]); these can appear together with N^[2] atoms, for example in $AE_2\text{Si}_5\text{N}_8$,^{6,7} or even with N^[4] atoms in BaYbSi₄N₇.⁸ Terminal Si–N bonds (N^[1]) are found in Ba₅Si₂N₆.⁹ Recent calculations on such compounds have shown that the N^[n] 2p-derived crystal orbitals which dominate the top of the valence band decrease in energy as n increases in a series of nitridosilicates ($1 \leq n \leq 4$).¹⁰ Second, the nitride anion is more polarizable than the oxide anion and one consequence of this is that edge-sharing of SiN₄ tetrahedra is not forbidden in nitridosilicates, as it is in oxosilicates, since the ensuing Si–Si repulsion is screened

* Author to whom correspondence should be addressed. E-mail: simon.clarke@chem.ox.ac.uk. Fax: +44 1865 272690. Tel: +44 1865 272600.

- (1) Petzow, G.; Herrmann, M. *Struct. Bonding* **2002**, *102*, 47.
- (2) Rosenflanz, A. *Curr. Opin. Solid State Mater. Sci.* **1999**, *4*, 453.
- (3) Schnick, W.; Huppertz, H.; Lauterbach, R. *J. Mater. Chem.* **1999**, *9*, 289.
- (4) Soignard, E.; Somayazulu, M.; Dong, J. J.; Sankey, O. F.; McMillan, P. F. *J. Phys.: Condens. Matter* **2001**, *13*, 557.

- (5) Kollisch, K.; Schnick, W. *Angew. Chem., Int. Ed.* **1999**, *38*, 357.
- (6) Schlieper, T.; Schnick, W. *Z. Anorg. Allg. Chem.* **1995**, *621*, 1037.
- (7) Schlieper, T.; Milius, W.; Schnick, W. *Z. Anorg. Allg. Chem.* **1995**, *621*, 1380.
- (8) Schnick, W.; Huppertz, H. *Angew. Chem., Int. Ed. Engl.* **1996**, *35*, 1983.
- (9) Yamane, H.; DiSalvo, F. J. *J. Alloys Compd.* **1996**, *240*, 33.
- (10) Fang, C. M.; Hintzen, H. T.; de With, G.; de Groot, R. A. *J. Phys.: Condens. Matter* **2001**, *13*, 67. Fang, C. M.; Li, Y. Q.; Hintzen, H. T.; de With, G. *J. Mater. Chem.* **2003**, *13*, 1480.

by the induced dipoles on the polarizable bridging anions.¹¹ (There is only one unconfirmed report of edge sharing of SiO₄ tetrahedra in a polymorph of SiO₂.¹²) Edge sharing of SiN₄ tetrahedra has been observed both in the silicon-rich BaSi₇N₁₀,¹³ synthesized by Schnick and co-workers at 1650 °C, and in the barium-rich Ba₅Si₂N₆,⁹ synthesized by Yamane and DiSalvo at 750 °C in molten sodium, in which isolated Si₂N₆¹⁰⁻ anions are composed of a pair of edge-sharing SiN₄ tetrahedra. Edge sharing of MN₄ tetrahedra has also been reported in several alkaline earth gallium and aluminum nitrides, including the isostructural pairs AE₃Ga₂N₄ (AE = Sr,¹⁴ Ba¹⁵) and AE₃Al₂N₃ (AE = Sr,¹⁶ Ba¹⁷) and Ca₃Ga₂N₄,¹⁴ which contrast with the vertex-sharing only of GaO₄ tetrahedra in gallates. Li₄Sr₃Ge₂N₆¹⁸ contains a [Ge₂N₆]¹⁰⁻ anion composed of a pair of edge-sharing GeN₄ tetrahedra. In addition to the BaSi₇N₁₀¹³ and Ba₅Si₂N₆⁹ stoichiometries described above, several other alkaline earth nitridosilicates are known, including the structurally related series AE₂Si₅N₈ (AE = Ca,⁶ Sr, Ba⁷) with exclusively vertex-sharing SiN₄ tetrahedra and the compounds AESiN₂ (AE = Be,¹⁹ Mg,^{20,21} Ca,²² Sr,²³ Ba²⁴) which have been reported but for which only the ordered wurtzite structures of BeSiN₂ and MgSiN₂ with three-dimensional frameworks of vertex-sharing SiN₄ tetrahedra are known. BaSiN₂ has been reported synthesized as a powder by solid-state reaction between binary barium and silicon nitrides,²⁴ but although a tentative orthorhombic unit cell was obtained by indexing the powder diffraction pattern, no suitable structural model could be deduced by comparison with isostoichiometric oxides. As part of a program investigating low-temperature approaches to ternary nitride synthesis by reacting intermetallic compounds with ammonia, which has received only very limited attention in the past,²⁵ we have synthesized bulk crystalline BaSiN₂ at much lower temperatures (550 °C) than previously used. Although we were unable to deduce a structural model on the basis of the information available from the powder diffraction pattern, we have determined the crystal structure of this compound by the analysis of single crystals grown from molten sodium at 900–1100 °C. Powder and single-crystal samples of SrSiN₂ and single crystals of CaSiN₂ have also been obtained enabling comparison of the structures of

Table 1. Contents of the Tantalum Tubes for Reactions Used to Synthesize Crystals of the Compounds AESiN₂ (AE = Ca, Sr, Ba)^a

compd	reacn temp/°C	NaN ₃ /mg	AE/mg	Si/mg	Na/mg
BaSiN ₂	1100	63	206	21	200
SrSiN ₂	1000	46	96	30	200
CaSiN ₂	1000	70	33	46	200

^a The amount of NaN₃ was chosen to give a maximum possible pressure inside the tube of 35 atm; the tantalum tubes used were of different volumes.

AESiN₂ for all alkaline earths and comparison with the structures of isostoichiometric oxides, chalcogenides, and pnictides.

Experimental Section

Synthesis. Most of the reactants and products used in this work are air-sensitive, so all manipulations of solids were carried out in a Glovebox Technology argon-filled recirculating drybox with a combined O₂ and H₂O content of less than 5 ppm. For the synthesis of single crystals, alkaline earth metal pieces (Ba, 99+%, Aldrich; Sr, 99%, Aldrich; Ca, 99.5%, ALFA), silicon (99.9999%, Alfa Aesar, finely ground in the drybox), sodium azide (99%, Aldrich), and sodium (99+%, BDH) were placed in a tantalum tube (9 mm outer diameter, 0.5 mm wall thickness, 120 mm long) which was sealed under 1 atm of purified argon and then sealed inside an evacuated silica ampule. The amount of NaN₃ used in each case was adjusted to keep the maximum possible nitrogen pressure constant at 35 atm for all temperatures, and approximately 200 mg of Na was added as a “flux”. For reactions carried out at 1100 °C with a Ba:Si molar ratio of 2:1, which were found to produce the largest yield of high-quality crystals, the contents of the tantalum tube were as follows: NaN₃, 63 mg; Ba, 206 mg; Si, 21 mg; Na, 200 mg. The tubes were heated in a chamber furnace at 3 °C min⁻¹ to temperatures of 900 or 1100 °C, soaked at these temperatures for 48 h, and then cooled at 0.1 °C min⁻¹ to 400 °C whence the furnace was switched off. The sodium was removed by sublimation under dynamic vacuum at 350 °C. Single crystals were extracted by dispersing the product in Paratone oil. The syntheses of crystals of SrSiN₂ and CaSiN₂ were carried out at 1000 °C, and the contents of the tantalum tubes were as summarized in Table 1.

High yields of the target phases were obtained in these reactions, although the crystals produced were often small and of poor quality. While the elements were found to be suitable starting materials for the syntheses carried out in molten sodium, binary alkaline earth nitrides can also be used as sources of the metals and of some of the nitrogen in the products. Sr₂N²⁶ was prepared on the 1.5 g scale by the reaction between freshly cut Sr pieces and flowing nitrogen gas (Air Products, oxygen free, and additionally cleaned by flowing over a Ti wire “getter” held at 800 °C) at 900 °C for 48 h. Stoichiometric amounts (i.e. Sr:Si = 1:1) of Sr₂N (189.3 mg) and Si (56 mg) were sealed in a tantalum tube with 150 mg of Na and 22 mg of NaN₃, and the tube was heated at 1100 °C. The product was pure white SrSiN₂ (powder and small crystals) according to laboratory powder X-ray diffraction (PXRD) measurements, and this sample was used for powder neutron diffraction (PND) measurements. Additionally, BaSiN₂ and SrSiN₂ were synthesized as bulk powders by reacting the intermetallics BaSi or SrSi with ammonia. BaSi was synthesized from stoichiometric amounts of the elements by reacting 2.49 g of barium lump (99+%, Aldrich, and with the oxide coating removed by filing) with 0.5093 g of silicon powder (99.9999%, Alfa Aesar) in a 9 mm diameter tantalum tube which was sealed under 1 atm of argon to avoid evaporation

- (11) Madden, P. A.; Wilson, M. *Chem. Soc. Rev.* **1996**, 339.
- (12) Weiss, A.; Weiss, A. *Z. Anorg. Allg. Chem.* **1954**, 276, 95.
- (13) Huppertz, H.; Schnick, W. *Chem.—Eur. J.* **1997**, 3, 249.
- (14) Clarke, S. J.; DiSalvo, F. J. *Inorg. Chem.* **1997**, 36, 1143.
- (15) Yamane, H.; DiSalvo, F. J. *Acta Crystallogr., Sect C: Cryst. Struct. Commun.* **1996**, 52, 760.
- (16) Blase, W.; Cordier, G.; Ludwig, M.; Kriep, R. *Z. Naturforsch., B* **1994**, 49, 501.
- (17) Ludwig, M.; Niewa, R.; Kniep, R. *Z. Naturforsch., B* **1999**, 54, 461.
- (18) Park, D. G.; Gál, Z. A.; DiSalvo, F. J. *J. Solid State Chem.* **2003**, 172, 166.
- (19) Rabenau, A.; Eckerlin, P. *Naturwissenschaften* **1959**, 46, 106.
- (20) David, J.; Laurent, Y.; Lang, J. *Bull. Soc. Fr. Mineral. Cristallogr.* **1970**, 93, 153.
- (21) Bruls, R. J.; Hintzen, H. T.; Metselaar, R.; Loong, C.-K. *J. Phys. Chem. Solids* **2000**, 61, 1285.
- (22) Laurent, Y.; Lang, J. *C. R. Acad. Sci. Paris* **1966**, 262, 103.
- (23) Gaudé, J.; Lang, J. *C. R. Acad. Sci. Paris* **1969**, 268, 1785.
- (24) Morgan, P. E. D. *J. Mater. Sci. Lett.* **1984**, 3, 131.
- (25) Guyader, J.; Maunay, M.; Lang, J. *C. R. Acad. Sci. Paris* **1971**, 272, 311.

- (26) Brese N. E.; O’Keeffe M. *J. Solid State Chem.* **1990**, 87, 134.

of barium.²⁷ The tantalum tube was protected inside an evacuated silica jacket and heated at 900 °C for 48 h. BaSi does not melt congruently, and the sample was therefore annealed at 825 °C for 25 days. The gray product was confirmed to be BaSi using laboratory PXRD. SrSi was synthesized in a similar way by reacting 2.9444 g of strontium pieces (99%, Aldrich) with 0.9438 g of silicon powder in a sealed tantalum tube at 1200 °C for 4 days, followed by annealing at 1130 °C for 30 days.

To form BaSiN₂, 1.8 g of finely ground BaSi was spread along the length of a 4 cm long alumina boat which was placed in a 22 mm internal diameter silica tube. The tube was placed inside a split tube furnace and purged with ammonia (NH₃, 99.98%, BOC, and cleaned further by storage over sodium). The temperature was raised to 550 °C at a rate of 7 °C min⁻¹ and maintained at this temperature under a flow of ammonia of approximately 3 dm³ h⁻¹ for a period of 24 h whence the flow tube was isolated from the ammonia flow and removed from the furnace allowing the sample to cool to room temperature. The tube was evacuated and returned to the drybox; the white product was ground and then heated at 900 °C under flowing ammonia for a further 24 h to improve the crystallinity. The reaction of SrSi with ammonia was accomplished in a similar way: SrSi was heated in anhydrous ammonia for periods of 24 h at 600, 800, and 1000 °C with intermediate regrinding in the drybox. In this case heating at 1000 °C was required to obtain a white, fully oxidized, product.

Chemical Analysis. Energy-dispersive analysis of X-rays (EDX) was carried out on single crystals using a JEOL JSM-840A scanning electron microscope equipped with an Oxford Instruments ISIS300 energy-dispersive X-ray analysis system. It was not possible to obtain quantitative analysis for nitrogen using this instrument. Combustion analysis for nitrogen on bulk powders was carried out using a Carlo Erber Strumentazione 1106 CHN analyzer.

X-ray Powder Diffraction. Some measurements were made using a Siemens D5000 diffractometer operating in Debye–Scherrer geometry with Cu Kα₁ radiation selected using a Ge(111) monochromator. The samples were ground with amorphous boron (1:1 mass ratio) to limit sample absorption and sealed in 1 mm diameter glass capillaries. Alternatively, measurements were made using a Phillips PW 1729/10 diffractometer operating in Bragg–Brentano geometry with Cu Kα₁/α₂ radiation and equipped with a diffracted beam monochromator. Samples were contained within an airtight sealed holder.

Single-Crystal X-ray Diffraction. Crystals protected under Paratone oil were mounted in a nylon loop and immobilized in the frozen oil at 150 K using an Oxford Instruments cooling system integral to the single-crystal diffractometer. High-redundancy data sets were collected down to 0.7 Å resolution using an Enraf-Nonius FR590 κCCD diffractometer using Mo Kα radiation (λ = 0.710 71 Å) achieved using a graphite monochromator. Data were analyzed with the DENZO-SMN programs.²⁸ Heavy atoms were located using direct methods, after which nitrogen atoms were located from difference Fourier maps. Analytical absorption corrections²⁹ were carried out in the cases of BaSiN₂ and SrSiN₂, and the structure refinements were completed using SHELXL-97.³⁰

Neutron Powder Diffraction. Time-of-flight powder neutron diffraction (PND) data were collected using the diffractometer POLARIS at the ISIS Facility, Rutherford Appleton Laboratory.

Table 2. Results of Single-Crystal X-ray and Neutron Refinements (at 298 and 4 K) of BaSiN₂

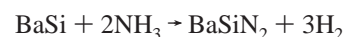
parameter	single crystal at 150 K	powder	
		298 K	4 K
formula	BaSiN ₂	BaSiN ₂	BaSiN ₂
radiation	Mo Kα, λ = 0.710 73 Å	Neutron	Neutron
instrument	Enraf-Nonius FR590 κCCD	POLARIS	POLARIS
space group	<i>Cmca</i>	<i>Cmca</i>	<i>Cmca</i>
fw	193.43	193.43	193.43
a/Å	5.6046(1)	5.60430(5)	5.6009(2)
b/Å	11.3605(3)	11.3655(1)	11.3490(4)
c/Å	7.5851(2)	7.59965(7)	7.5844(3)
V/Å ³	482.95(2)	484.06(1)	482.11(5)
Z	8	8	8
ρ _{calc} /Mg m ⁻³	5.321	5.309(1)	5.330(1)
no. of variables	25	89	86
R1	0.0138		
wR2	0.0282		
χ ²		1.110	0.885
wRp		0.0115	0.0074
R _p ²		0.0197	0.0223

Measurements were made on BaSiN₂ derived from the nitridation of BaSi at 900 °C and on a sample of SrSiN₂ obtained using the sodium flux route at 1100 °C. Diffraction patterns were measured in the *d*-spacing range 0.5 < *d* < 8 Å by means of three banks of detectors located at scattering angles 2θ of 35° (³He tube detector), 90° (ZnS scintillator), and 145° (³He tube detector, highest resolution bank: Δ*d*/*d* = 5 × 10⁻³) for a total integrated proton current at the production target of 380 μA h for 2.0 g of BaSiN₂ and 1445 μA h for 0.25 g of SrSiN₂ at room temperature. The samples were contained in cylindrical thin-walled vanadium cans sealed under 1 atm of Ar with indium gaskets. Data for BaSiN₂ at 4 K (372 μA h) were obtained in an “ILL orange” cryostat. PND, and where appropriate PXRD, data were analyzed using the Rietveld profile refinement suite GSAS.³¹ Refinement against data collected on POLARIS was carried out using all three detector banks simultaneously.

Results

BaSiN₂. Clear/colorless crystals of BaSiN₂ were isolated from reactions in molten sodium with a Ba:Si ratio of 2:1 at 900 and 1100 °C. EDX data produced a Ba:Si ratio of 0.53- (3):0.47(3), and laboratory PXRD showed that BaSiN₂ was the majority phase in both reactions. The analysis of single-crystal data showed that higher quality crystals (mosaic spread of 0.7–1.0 °) were obtained in the reactions at 1100 °C compared with those obtained in reactions at 900 °C (mosaic spread of 1.5–1.7°). Structure solution by direct methods and subsequent refinement yielded a model in space group *Cmca* with *a* = 5.6046(1) Å, *b* = 11.3605(3) Å, *c* = 7.5851(2) Å, and *Z* = 8, largely confirming Morgan’s proposal.²⁴ The refinement results are shown in Table 2, and the atomic positions and equivalent isotropic displacement parameters are listed in Table 3.

The mass change during the nitridation of BaSi by ammonia at 550 °C was consistent with full oxidation to form BaSiN₂:



(27) Merlo, F.; Fornasini, M. L. *J. Less Common Met.* **1967**, *13*, 603.

(28) Nonius, Collect, Denzo, Scalepack, Sortav: *Kappa CCD Program Package*; Nonius BV: Delft, The Netherlands, 1998.

(29) Alcock, N. *Cryst. Comput.* **1970**, 271.

(30) Sheldrick, G. *A Program for Crystal Structure Determination*, release 97-2; University of Gottingen: Gottingen, Germany, 1997.

(31) Larson, A.; von Dreele, R. B. *The General Structure Analysis System*; Los Alamos National Laboratory: Los Alamos, NM, 1985.

Table 3. Atomic Parameters for BaSiN₂ Obtained from Single-Crystal X-ray Diffraction Data at 150 K and Powder Neutron Diffraction Data at 298 and 4 K^a

atom	site	x	y	z	100U _{iso,eq} /Å ²
Single-Crystal X-ray Diffraction					
Ba	8f	0	0.335 56(1)	0.065 23(2)	0.450(7)
Si	8f	0	0.049 41(6)	0.140 45(9)	0.29(1)
N1	8f	0	0.398 1(2)	0.419 2(3)	0.44(4)
N2	8e	0.25	0.097 8(2)	0.25	0.59(4)
Powder Neutron Diffraction					
Ba	8f	0	0.335 82(4)	0.0651 3(6)	0.49(1)
			[0.335 72(4)]	[0.065 24(6)]	[0.056(6)]
Si	8f	0	0.049 38(4)	0.140 03(8)	0.29(1)
			[0.049 46(5)]	[0.139 91(9)]	[0.18(2)]
N1	8f	0	0.398 10(2)	0.419 97(3)	0.60(1)
			[0.398 04(3)]	[0.419 34(4)]	[0.38(1)]
N2	8e	0.25	0.097 15(2)	0.25	0.79(1)
			[0.097 95(3)]		[0.46(1)]

^a Values in brackets are obtained from refinement against neutron powder diffraction data at 4 K.

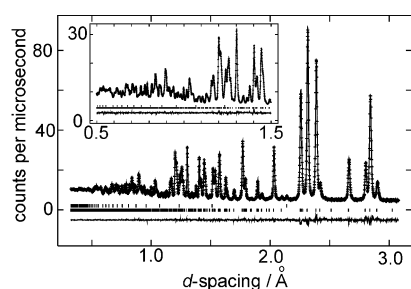


Figure 1. Results of Rietveld refinement of the structure of BaSiN₂ at 298 K against POLARIS data (145° detector bank). The measured (points), calculated, (line) and difference (lower line) profiles are shown. Tick marks indicate allowed reflections for the BaSiN₂ phase (lower set) and the vanadium sample container (upper set). The inset shows a magnification of the low *d*-spacing region.

Combustion analysis of the white powder yielded 13.5-(2)% by mass nitrogen, corresponding to a stoichiometry of BaSiN_{1.87(3)}. The powder diffraction pattern closely resembled that reported previously²⁴ and that obtained by PXRD analysis of the samples obtained from molten sodium. The material obtained after further reaction with ammonia at 900 °C was more crystalline (Bragg peaks 80% of the width of those of the sample prepared at 550 °C) and was used in further structural analysis. Refinement against PND data collected at 298 K and at 4 K, using as a starting model that obtained from the results of single-crystal analysis, proceeded without incident confirming the single-crystal result. The refinement results are presented in Table 2, and the fit at 298 K is shown in Figure 1. The atomic parameters at 298 and 4 K are compared with those of the single-crystal solution at 150 K in Table 3.

SrSiN₂. Extremely air-sensitive clear/colorless crystals were extracted from the gray powder obtained by the reaction between strontium and silicon (Sr:Si = 1:1) under nitrogen in molten sodium at 1000 °C (Table 1). EDX analysis indicated a Sr:Si ratio of 0.6:0.4, but this analysis was hampered by overlap between the main Sr and Si lines using this technique. The crystals were extremely thin with a needlelike habit and had a high mosaic spread (2°) resulting in noisy data. However, structure solution by direct methods and subsequent refinement confirmed that the stoichiometry

Table 4. Results for Structure Refinements of SrSiN₂ against Single-Crystal X-ray and Powder Neutron Diffraction Measurements

parameter	single crystal	powder
formula	SrSiN ₂	SrSiN ₂
radiation	Mo Kα, λ = 0.710 73 Å	neutrons
instrument	Enraf-Nonius FR590 κCCD	POLARIS
<i>T</i> /K	150(2)	298
space group	<i>P</i> 2 ₁ / <i>c</i>	<i>P</i> 2 ₁ / <i>c</i>
<i>f</i> _w	143.73	143.73
<i>a</i> /Å	5.9750(5)	5.98139(6)
<i>b</i> /Å	7.2826(7)	7.32121(7)
<i>c</i> /Å	5.4969(4)	5.50425(6)
β/deg	113.496(4)	113.518(1)
<i>V</i> /Å ³	219.36(3)	221.014(5)
<i>Z</i>	4	4
ρ _{calc} /Mg m ⁻³	4.352	4.319
<i>R</i> 1	0.0458	
w <i>R</i> 2	0.0893	
χ ²		1.832
w <i>R</i> _p		0.0115
<i>R</i> _{F²}		0.0275

Table 5. Refined Atomic Parameters for SrSiN₂

atom	site	x	y	z	100U _{iso,eq} /Å ²
Single-Crystal X-ray Diffraction at 150 K					
Sr	4e	0.339 3(1)	0.5724(1)	0.175 6(1)	1.06(3)
Si	4e	0.107 7(4)	0.1419(3)	0.0671(4)	1.00(4)
N1	4e	0.210(1)	0.5905(8)	0.585(1)	1.0(1)
N2	4e	0.219(1)	0.2252(8)	0.385(1)	1.2(1)
Powder Neutron Diffraction at 298 K					
Sr	4e	0.338 76(9)	0.573 82(8)	0.175 5(1)	0.83(3)
Si	4e	0.104 9(2)	0.141 9(1)	0.068 2(2)	0.33(4)
N1	4e	0.208 29(8)	0.587 73(6)	0.584 06(9)	0.73(2)
N2	4e	0.215 43(9)	0.224 39(6)	0.386 2(1)	0.89(2)

was SrSiN₂ and yielded a model in the monoclinic space group *P*2₁/*c* (No. 14) with *a* = 5.9750(5) Å, *b* = 7.2826(7) Å, *c* = 5.4969(4) Å, β = 113.496(4)°, and *Z* = 4. The PXRD pattern of the sample which yielded these crystals of SrSiN₂ closely resembled that reported previously for an incompletely characterized sample of SrSiN₂.²³ Indeed this route is a convenient one for the synthesis of bulk SrSiN₂, and a sample prepared using a modification of this route with Sr₂N as the source of Sr (see above) at 1100 °C was the one used in the PND measurement. This measurement confirmed the monoclinic model and ruled out an alternative, but lower probability, orthorhombic cell. The refinement results from single-crystal X-ray and PND analysis are shown in Table 4, and the atomic positions and equivalent isotropic displacement parameters are listed in Table 5. The results of the refinement against PND data are shown in Figure 2. The formation of bulk SrSiN₂ by the reaction of SrSi with anhydrous ammonia is more difficult than in the case of BaSiN₂: while the reaction with BaSi is complete at 550 °C, and heating at 900 °C merely improves crystallinity, the mass gain indicating full conversion to white SrSiN₂ was only accomplished after reactions at 1000 °C. Furthermore, while the full widths at half-maximum of the Bragg peaks of the samples of BaSiN₂ and SrSiN₂ used in the PND investigations were similar (approximately 0.25° measured using the Philips laboratory X-ray diffractometer), the bulk sample of SrSiN₂ prepared at 1000 °C from the reaction of SrSi with ammonia had Bragg peaks 40% broader than those of the sample used in the PND measurement. Comparative

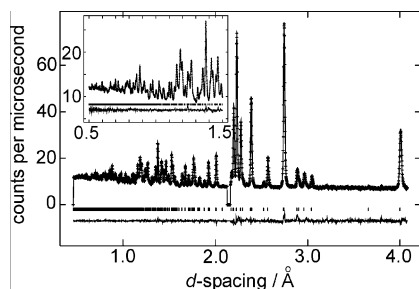


Figure 2. Results of Rietveld refinement of the structure of SrSiN₂ at 298 K against POLARIS data (90° detector bank). The measured (points), calculated (line), and difference (lower line) profiles are shown. Tick marks indicate allowed reflections for SrSiN₂. A reflection at 2.14 Å due to the vanadium sample container has been excluded from the refinement. The inset shows a magnification of the low *d*-spacing region.

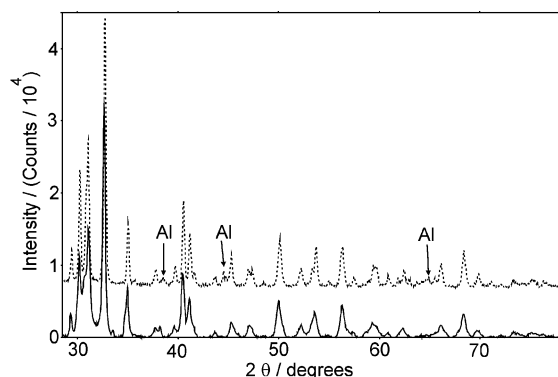


Figure 3. X-ray diffractograms (Cu K α_1/α_2 radiation) for the sample of SrSiN₂ prepared using the sodium flux method at 1100 °C and used in the PND measurements (top, dotted), and a sample prepared by the reaction between SrSi and flowing ammonia at 1000 °C (bottom, solid). The dotted line has been offset along the intensity axis for clarity, and peaks arising from the aluminum sample holder are marked.

Table 6. Results of Single-Crystal X-ray Refinement of CaSiN₂

formula	CaSiN ₂
radiation	Mo K α , $\lambda = 0.71073$ Å
instrument	Enraf-Nonius FR590 κ CCD
physical form	single cryst
<i>T</i> /K	150
space group	<i>Pbca</i>
<i>f</i> _w	96.19
<i>a</i> /Å	5.1229(3)
<i>b</i> /Å	10.2074(6)
<i>c</i> /Å	14.8233(9)
<i>V</i> /Å ³	775.13(8)
<i>Z</i>	16
ρ_{calc} /Mg m ⁻³	3.297
R1	0.0406
wR2	0.0818

laboratory powder X-ray diffractograms shown in Figure 3 confirm that nitridation by ammonolysis is viable for the formation of bulk SrSiN₂.

CaSiN₂. Clear/colorless platelets obtained from a reaction in molten sodium with Ca:Si ratio 1:2 were found to have a Ca:Si ratio of 0.516(5):0.484(5) by EDX. The crystals were often twinned and with a high mosaicity (2°), but a satisfactory solution was determined by direct methods and subsequent refinement. CaSiN₂: space group *Pbca* (No. 61), *a* = 5.1229(3) Å, *b* = 10.2074(6) Å, *c* = 14.8233(9) Å, *Z* = 16. The refinement results are shown in Table 6, and the atomic positions and equivalent isotropic displacement

Table 7. Refined Atomic Parameters for CaSiN₂ Determined at 150 K

atom	site	x	y	z	100 <i>U</i> _{iso,eq} /Å ²
Ca1	8c	0.2414 (1)	0.009 68(7)	0.065 00(4)	1.19(2)
Ca2	8c	0.3462(1)	0.274 08(7)	0.187 59(4)	1.15(2)
Si1	8c	0.2265(2)	0.016 63(9)	0.312 08(6)	0.84(2)
Si2	8c	0.3172(2)	0.270 03(9)	0.437 22(6)	0.89(2)
N1	8c	0.0949(6)	0.477 4(3)	0.215 5(2)	1.13(6)
N2	8c	0.1495(6)	0.276 1(3)	0.035 4(2)	1.25(7)
N3	8c	0.1972(5)	0.426 8(3)	0.409 0(2)	1.11(6)
N4	8c	0.2762(6)	0.179 8(3)	0.338 2(2)	1.27(6)

parameters are listed in Table 7. The simulated PXRD pattern closely resembles that reported for material of composition CaSiN₂.²²

Discussion

Structures of BaSiN₂ and SrSiN₂. The results of the structural analysis of BaSiN₂ indicate a new structure type unlike that of any iso-stoichiometric oxide or nitride analogues, as suggested by the results of Morgan.²⁴ A search of the ICSD and MDF databases revealed no matches for the Pearson symbol of oC32 and Wyckoff sequence F^{3e} for any compounds of this stoichiometry. The structure is shown in Figure 4: pairs of SiN₄ tetrahedra share edges to form “bow-tie” units Si₂N₆, previously identified in Ba₅Si₂N₆⁹ and BaSi₇N₁₀.¹³ In BaSiN₂ these units condense by vertex sharing of the four remaining unshared vertexes to form puckered two-dimensional sheets separated by barium ions. The analysis of PND data confirmed the full occupancy of the anion site by nitride and showed that the structure is unchanged on cooling to 4 K. The structure of SrSiN₂ is closely related to that of BaSiN₂, and the two structures are compared in Figures 4 and 5. Selected bond lengths and angles for BaSiN₂, determined from both single-crystal X-ray and PND data, are listed in Table 8, and the corresponding values determined for SrSiN₂ are listed in Table 9.

The detailed diagram of the Si₂N₆ unit of BaSiN₂ in Figure 4 shows that while the N2–Si–N2 angle of 109.18(8)° (Table 8) is close to the ideal tetrahedral angle, the N1–Si–N1 angle associated with the shared edge is greatly reduced to 94.8(1)°. Furthermore, the Si–N1 distances of 1.781(2) and 1.777(2) Å are substantially longer than the two Si–N2 distances of 1.7191(8) Å. These are consequences of repulsion between Si atoms separated by the shared tetrahedral edge, and these angles and the differences between the mean Si–N(“bridging”) and Si–N(“terminal”) distances in the Si₂N₆ units of BaSi₇N₁₀¹³ and Ba₅Si₂N₆⁹ are fairly similar. In Ba₂Si₅N₈,⁷ with only corner-sharing SiN₄ tetrahedra, and including some cases of three tetrahedra sharing a common vertex (N^[3]), there is a wide range of Si–N distances (1.666–1.797 Å), but the N–Si–N angles are all in the range 103–115°. While the corresponding bond lengths and angles of SrSiN₂ (Figure 4, Table 9) are similar to those of BaSiN₂, Figure 5 shows that the effect of decreasing the size of the alkaline earth cation from Ba²⁺ to Sr²⁺ is distortion of the sheets of corner-linked Si₂N₆ units, by rotation about the linkages between Si₂N₆ units and lowering of the symmetry. In α -Ca₃Ga₂N₄,¹⁴ also depicted in Figure 5, the [GaN₂]³⁻ polyanion has the same topology

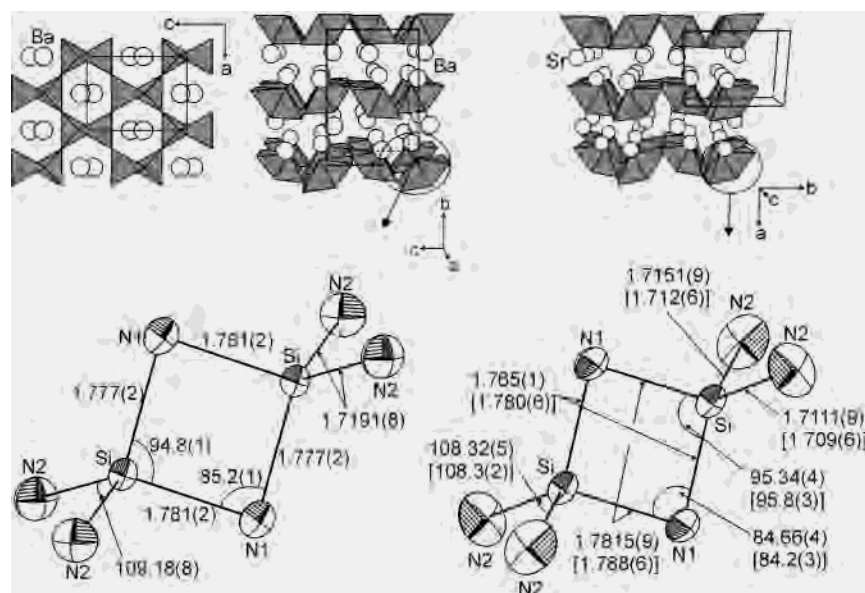


Figure 4. Crystal structures of BaSiN₂ (top: left and center) and SrSiN₂ (top: right) showing Si₂N₆ edge-sharing units linked at their remaining vertices to form layers. In the detailed views of the Si₂N₆ unit in BaSiN₂ (bottom: left), bond lengths (in Å) and angles (in deg) and 99% displacement ellipsoids are shown determined from single-crystal X-ray measurements at 150 K. For SrSiN₂ (bottom: right), 99% displacement ellipsoids are derived from the refinement against PND data at 298 K along with corresponding bond distances (in Å) and angles (in deg); bond distances obtained from refinement against single-crystal X-ray data are in brackets. Full lists of comparative bond lengths and angles are given in Tables 8 and 9. A view of SrSiN₂ perpendicular to the layers appears in Figure 5.

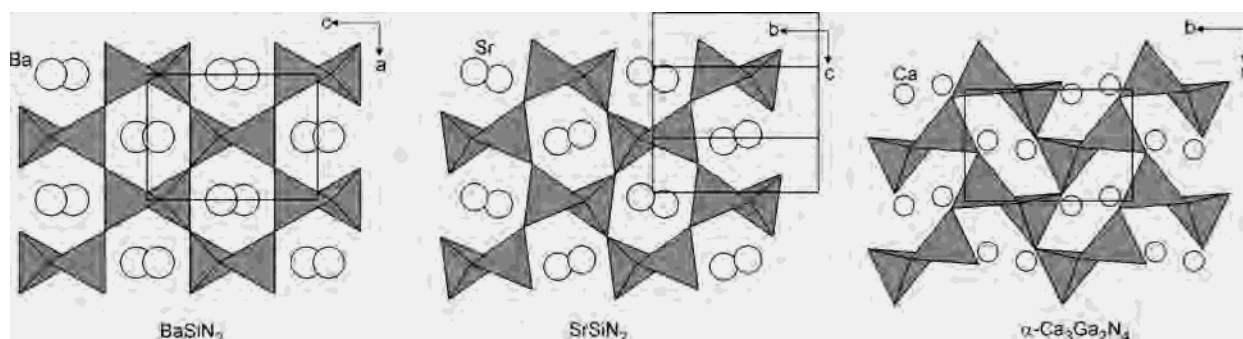


Figure 5. Comparison of the similar two-dimensional frameworks composed of pairs of edge-sharing tetrahedra joined at their remaining vertices to form puckered two-dimensional layers. The structure is flexible, and the figure shows the effect of increasing the size of the alkaline earth cations accommodated in and between the layers in a series of main group ternary nitrides. The structure of α -Ca₃Ga₂N₄ is described in ref 14.

Table 8. Selected Bond Lengths (Å) and Angles (deg) for BaSiN₂^a

bond length/angle	single crystal 150 K	neutron 298 K	neutron 4 K
Si–N1	1.781(2)	1.7778(6)	1.7763(6)
Si–N1	1.777(2)	1.7758(7)	1.7759(8)
Si–N2 [2]	1.7191(8)	1.7190(3)	1.7207(4)
Ba–N1 [2]	2.8935(6)	2.8923(2)	2.8907(2)
Ba–N1	2.877(2)	2.8805(6)	2.8745(6)
Ba–N1	2.777(2)	2.7851(5)	2.7772(5)
Ba–N2 [2]	2.8730(6)	2.8800(4)	2.8712(4)
Ba–N2 [2]	3.350(2)	3.3615(5)	3.3475(5)
Si–Si	2.408(1)	2.406(1)	2.401(1)
N2–Si–N2	109.18(8)	109.19(3)	108.93(4)
N1–Si–N1	94.8(1)	94.79(3)	94.95(3)
N2–Si–N1 [2]	115.60(8)	115.42(2)	115.61(3)
N2–Si–N1 [2]	110.40(6)	110.61(2)	110.48(3)
Si–N1–Si	85.2(1)	85.20(2)	85.05(3)
Si–N2–Si	142.7(2)	143.19(3)	142.69(4)

^a The numbers in brackets indicate the number of bonds or angles of a particular type.

as the [SiN₂]²⁻ polyanion in BaSiN₂ and SrSiN₂ but is distorted to an even greater degree than that in SrSiN₂.

The distortions are presumably driven by the coordination requirements of the electropositive cations. In BaSiN₂, Ba

Table 9. Selected Bond Lengths (Å) and Angles (deg) for SrSiN₂

bond length/angle	single crystal 150 K	SrSiN ₂ neutron 298 K
Si–N1	1.788(6)	1.7815(9)
Si–N1	1.780(6)	1.765(1)
Si–N2	1.709(6)	1.7111(9)
Si–N2	1.712(6)	1.7151(9)
Sr–N1	2.564(6)	2.5862(6)
Sr–N1	2.658(6)	2.6600(7)
Sr–N1	2.753(6)	2.7620(7)
Sr–N1	3.027(6)	3.0317(7)
Sr–N2	2.618(6)	2.6286(7)
Sr–N2	2.980(6)	3.0193(7)
Sr–N2	3.001(6)	3.0273(8)
Sr–N2	3.145(6)	3.1588(7)
Si–Si	2.391(4)	2.388(2)
N2–Si–N2	108.3(2)	108.32(5)
N1–Si–N1	95.8(3)	95.34(4)
N2–Si–N1	115.8(3)	115.80(5)
N2–Si–N1	117.5(3)	117.89(6)
N2–Si–N1	111.4(3)	111.14(5)
N2–Si–N1	107.1(3)	107.30(5)
Si–N1–Si	84.2(3)	84.66(4)
Si–N2–Si	135.6(4)	135.82(6)

is coordinated by six nitrogen atoms at distances of between 2.77 and 2.90 Å and two further ions are located at 3.350(2)

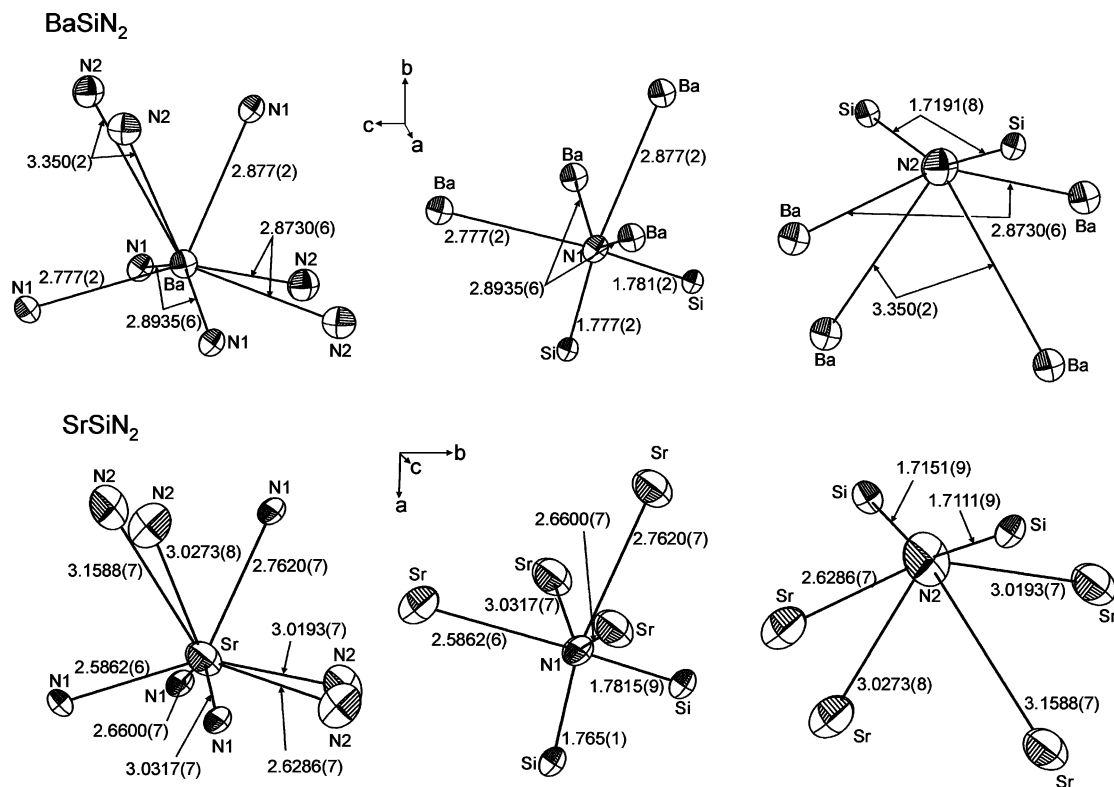


Figure 6. Comparative coordination geometries around the barium, strontium, and nitrogen atoms in BaSiN_2 (above) and SrSiN_2 (below). Displacement ellipsoids are shown at the 99% level, and the diagrams have the same orientations with respect to the crystallographic axes as the corresponding structure diagrams in Figure 4. The displacement ellipsoids and bond lengths (in Å) for BaSiN_2 are from the single-crystal X-ray refinement at 150 K. For SrSiN_2 , the corresponding parameters are derived from the refinement against PND data at 298 K, because the single crystal was of a relatively poor quality. Full lists of the bond lengths derived from different measurements are given in Tables 8 and 9.

Å as shown in Figure 6. In SrSiN_2 , only four nitride ions are located between 2.55 and 2.77 Å from Sr, and there are four other nitride ions at long bonding distances of between 2.97 and 3.13 Å. Both nitrogen atoms in BaSiN_2 are coordinated by two Si atoms and four Ba atoms in highly distorted octahedral arrangements as shown in Figure 6. N2, which links two adjacent Si_2N_6 units by their vertexes, is more strongly bonded to Si than N1, which links two SiN_4 tetrahedra at an edge to form the Si_2N_6 units. Correspondingly, the mean Ba–N1 distance of 2.86 Å is shorter than the mean Ba–N2 distance of 3.11 Å. The coordinations of the nitrogen atoms in SrSiN_2 (Figure 6) are geometrically similar to those in BaSiN_2 , although with lower symmetry as a consequence of the distortion on decreasing the size of the alkaline earth cation.

Structure of CaSiN_2 . CaSiN_2 , like the analogous compounds of the lighter alkaline earths, contains SiN_4 tetrahedra which are joined only at their vertexes. The structure of CaSiN_2 is shown in Figure 7, and bond lengths and angles are listed in Table 10. Crystals of CaSiN_2 have recently been prepared independently by Ottinger and Nesper,³² who have determined the same structure as that reported here. This structure is evidently more stable under the experimental conditions employed for CaSiN_2 synthesis than the BaSiN_2 -type structure with a framework more heavily distorted than in SrSiN_2 , such as that found in $\alpha\text{-Ca}_3\text{Ga}_2\text{N}_4$ ¹⁴ (Figure 5).

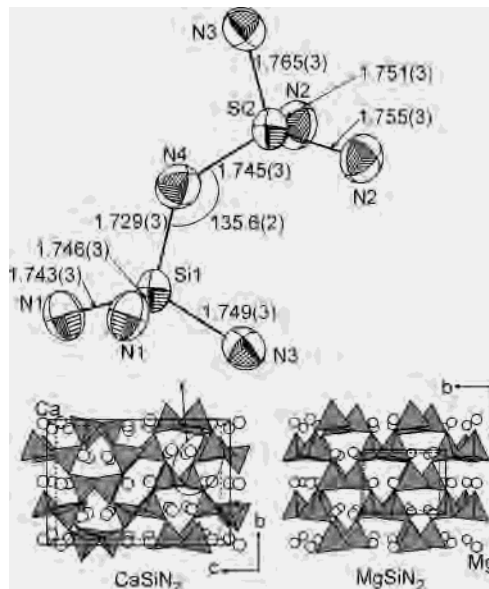


Figure 7. Cristobalite-derived structure of CaSiN_2 compared with the wurtzite-derived structure of MgSiN_2 .²¹ Displacement ellipsoids for the detail of the SiN_4 tetrahedra of CaSiN_2 determined at 150 K from X-ray single-crystal data are shown at the 99% level. A full list of bond lengths and angles is given in Table 10.

The arrangement of vertex-linked tetrahedra in CaSiN_2 is the D1-type tilting distortion of the idealized C9-type β -cristobalite framework.³³ If the alkaline earth cation is

(32) Ottinger, F.; Nesper, R. *Acta Crystallogr., Sect. A: Foundations of Crystallography* **2002**, *58* (Supplement), C337.

(33) Thompson, J. G.; Withers, R. L.; Palethorpe, S. R.; Melnitchenko, A. *J. Solid State Chem.* **1998**, *141*, 29.

Table 10. Selected Bond Lengths (Å) and Angles (deg) for CaSiN₂

Si1–N4	1.729(3)	Ca1–N1	2.406(3)	Ca1–N2	2.794(3)
Si1–N1	1.743(3)	Ca1–N3	2.412(3)	Ca1–N3	3.022(3)
Si1–N1	1.746(3)	Ca1–N3	2.431(3)		
Si1–N3	1.749(3)	Ca1–N2	2.488(3)		
Si2–N4	1.745(3)	Ca2–N4	2.434(3)	Ca2–N3	2.778(3)
Si2–N2	1.751(3)	Ca2–N4	2.458(3)	Ca2–N1	2.827(3)
Si2–N2	1.755(3)	Ca2–N2	2.470(3)		
Si2–N3	1.765(3)	Ca2–N1	2.477(3)		
N4–Si1–N1	109.1(1)	N4–Si2–N2	109.3(2)	Si1–N1–Si1	129.4(2)
N4–Si1–N1	114.4(1)	N4–Si2–N2	119.8(2)	Si2–N2–Si2	131.2(2)
N1–Si1–N1	104.5(1)	N2–Si2–N2	107.07(9)	Si1–N3–Si2	126.3(2)
N4–Si1–N3	106.7(1)	N4–Si2–N3	103.7(1)	Si1–N4–Si2	135.6(2)
N1–Si1–N3	115.9(1)	N2–Si2–N3	111.2(1)		
N1–Si1–N3	106.4(1)	N2–Si2–N3	105.6(1)		

smaller than Ca²⁺, the structure adopted is based on a different arrangement of vertex-linked tetrahedra, and MgSiN₂^{20,21} and BeSiN₂¹⁹ have a cation-ordered wurtzite-type structure. Indeed the same relationship exists in the alkali metal gallates: MgSiN₂ and BeSiN₂ are isostructural with one polymorph of NaGaO₂,³⁴ while CaSiN₂ is isostructural with KGaO₂.³⁴ Although the relationship between the structures of MgSiN₂ and CaSiN₂ is not a simple one, Figure 7 compares the two structures showing that the orientation of the SiN₄ tetrahedra in MgSiN₂ results in a noncentrosymmetric structure, as found for the wurtzite archetype. CaGeN₂ has been reported³⁵ with the B1-type (β -KCoO₂) tilting distortion of the β -cristobalite structure. All the nitrogen atoms in CaSiN₂ are at the shared vertexes of a pair of vertex-shared tetrahedra. The mean of the Si–N distances in CaSiN₂ (Table 10) is 1.748(9) Å; this is similar to the mean values in BaSiN₂ (1.75(3) Å) and SrSiN₂ (1.75(4) Å), although in these compounds in which there is some edge-sharing of SiN₄ tetrahedra, and consequently two types of Si–N bond, as discussed above, the standard deviations in the values are much larger. Ca1 is surrounded by four N atoms located between 2.40 and 2.49 Å (i.e. at distances similar to the sum of the ionic radii³⁶) and by two further N atoms which complete an approximately octahedral geometry. Ca2 is in a highly distorted octahedral environment, again with four shorter Ca–N distances (between 2.43 and 2.48 Å) and two longer distances of around 2.8 Å. Since all the SiN₄ tetrahedra share all their vertexes, all the nitrogen atoms are coordinated to two Si atoms. All the N atoms are also coordinated by two further Ca atoms located 2.40–2.49 Å distant. N1 and N2 are coordinated by a further Ca atom each at around 2.8 Å to give distorted five-coordinate geometries. N3 is coordinated by two further Ca atoms at 2.777(3) and 3.023(3) Å and might be considered six-coordinate, while N4 is probably best considered four-coordinate in a distorted tetrahedral environment. Distances are listed in Table 10.

Comparison with Other Compounds. The structure of BaSiN₂ is one that has no known analogue in oxide chemistry and which, like many other nitridosilicates, contains edge-shared SiN₄ tetrahedra. These are not found in the analogous oxides because this would entail too much repulsion of the

tetrahedral atom across the shared edge. All the members of the AESiN₂ (*AE* = Be, Mg, Ca, Sr, Ba) family contain nitrogen atoms exclusively coordinated by two silicon atoms (N^[2]), but while BaSiN₂ and SrSiN₂ have a framework containing both edge- and vertex-sharing SiN₄ tetrahedra, the isostructural compounds of the smaller alkaline earths adopt structures in which the [SiN₂]²⁻ anionic framework is exclusively constructed from vertex-sharing tetrahedra. This trend for the larger alkaline earths to favor condensation of the tetrahedra at their edges is also found in other nitrides: Ba₃Ga₂N₄¹⁵ and Sr₃Ga₂N₄¹⁴ contain infinite chains of GaN₄ tetrahedra each sharing a pair of opposing edges, while α -Ca₃Ga₂N₄,¹⁴ with a framework similar to that in BaSiN₂, has both edge- and vertex-sharing, (but β -Ca₃Ga₂N₄³⁷ is constructed from GaN₄ tetrahedra which share only vertexes). The condensation of SiN₄ tetrahedra by edge sharing is presumably driven by the coordination requirements of the larger alkaline earth cations and is possible because nitride is sufficiently polarizable to accommodate the close approach of silicon atoms.¹¹ Edge-sharing of tetrahedra in main group compounds containing the more polarizable heavier chalcogenides and pnictides is common: Ca₃Al₂As₄³⁸ is isostructural with α -Ca₃Ga₂N₄,¹⁴ with a framework similar to that in BaSiN₂ and SrSiN₂, but we have been unable to identify any compounds isostructural with BaSiN₂ or SrSiN₂. KGaS₂³⁹ contains a double layer of all-vertex-linked GaS₄ tetrahedra, while, with the larger Cs⁺ ion, the GaS₄ tetrahedra share a pair of opposite edges with two neighboring tetrahedra, as in Sr₃Ga₂N₄¹⁴ and Ba₃Ga₂N₄,¹⁵ to form infinite chains in CsGaS₂⁴⁰ (the structure of Rb analogue has not been reported). LaCuS₂⁴¹ matches the space group, Pearson symbol (mP16), and Wyckoff sequence (e⁴) of SrSiN₂ but is not isostructural because although it does contain layers composed of Cu₂S₆ units comprising a pair of edge-sharing CuS₄ tetrahedra, in this case the S atoms participating in edge-sharing are coordinated by a further Cu atom in a neighboring unit producing S^[3] and some S atoms are coordinated by only one Cu atom (S^[1]). TaCoTe₂ and NbCoTe₂⁴² contain layers of edge- and vertex-sharing CoTe₄ tetrahedra forming layers similar to those in BaSiN₂ and SrSiN₂ and with Co–Co bonds across the shared tetrahedral edges. However, in these cases the group 5 metal occupies 5-coordinate sites within the layers, and these are truly layered compounds. In NaAuSe₂,⁴³ the [AuSe₂]⁻ framework is the direct analogue of the framework in BaSiN₂ and SrSiN₂ but with SiN₄ tetrahedra replaced by AuSe₄ square planar units as expected for Au^{III}.

Conclusions. We have shown that the oxidative nitridation of intermetallics using ammonia is a convenient route for

(34) Müller, H.-P.; Hoppe, R. Z. *Anorg. Allg. Chem.* **1992**, *611*, 73.

(35) Maunay, M.; Guyader, J.; Laurent, Y.; Lang, J. *Bull. Soc. Fr. Mineral. Cristallogr.* **1971**, *94*, 347.

(36) Shannon, R. D. *Acta Crystallogr.* **1976**, *A32*, 751.

(37) Clarke, S. J.; DiSalvo, F. J. *J. Alloys Compd.* **1998**, *274*, 118.

(38) Cordier, G.; Czech, E.; Jakowski, M.; Schäfer, H. *Rev. Chim. Miner.* **1981**, *18*, 9.

(39) Lemoine, P.; Carre, D.; Guittard, M. *Acta Crystallogr.* **1984**, *C40*, 910.

(40) Schmitz, D.; Bronger, W. Z. *Naturforsch., B* **1975**, *30*, 491.

(41) Julien-Pouzol, M.; Jaulmes, S.; Mazurier, A.; Guittard, M. *Acta Crystallogr.* **1981**, *B37*, 1901.

(42) Li, J.; McCulley, F.; McDonnell, S. L.; Masiocchi, N.; Proserpio, D. M.; Sironi, A. *Inorg. Chem.* **1993**, *32*, 4829.

(43) Park, Y.; Kanatzidis, M. G. *J. Alloys Compd.* **1997**, *257*, 137.

the synthesis of bulk ternary nitrides, which in the case of BaSiN_2 , for example, may be employed at relatively low temperatures. We are currently investigating the wide use of this route in the synthesis of novel nitrides. The structures of BaSiN_2 and SrSiN_2 appear to have no direct analogues in oxide chemistry or in the chemistry of the heavier chalcogenides or pnictides.

Acknowledgment. We are grateful to the U.K. Engineering and Physical Sciences Research Council for funding under Grant GR/R53296. S.J.C. acknowledges the further

research support of the Royal Society. We thank Dr. N. Charnley (Department of Earth Sciences, University of Oxford) for assistance with the EDX analysis and Dr. R. I. Smith (ISIS facility) for assistance with the neutron diffraction investigations.

Supporting Information Available: X-ray crystallographic data in CIF format. This material is available free of charge via the Internet at <http://pubs.acs.org>.

IC049901P